



M29F102BB

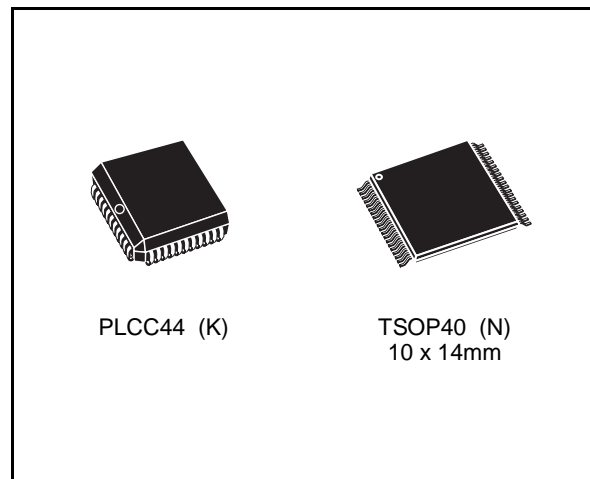
1 Mbit (64Kb x16, Boot Block) Single Supply Flash Memory

DATA BRIEFING

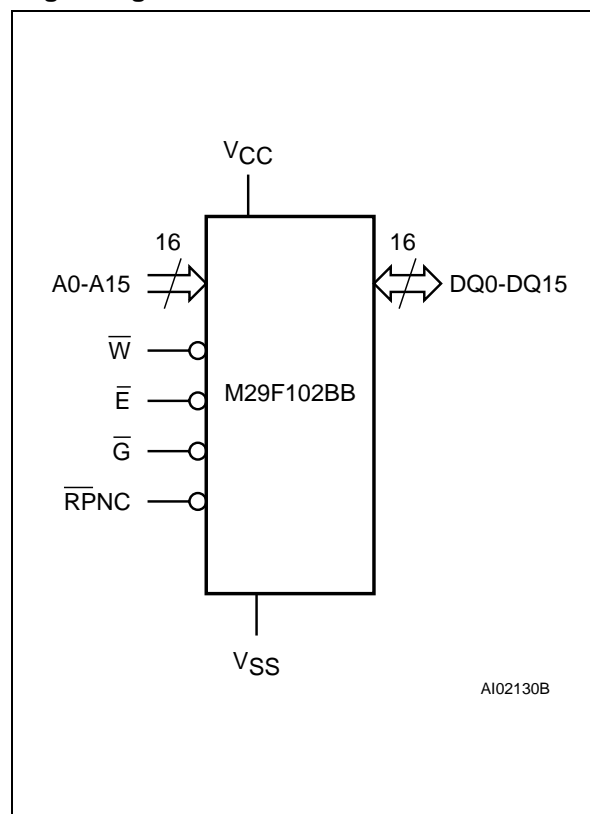
- 5V±10% SUPPLY VOLTAGE for PROGRAM, ERASE and READ OPERATIONS
- FAST ACCESS TIME: 35ns
- FAST PROGRAMMING TIME: 10µs typical
- PROGRAM/ERASE CONTROLLER (P/E.C.)
 - Program Word-by-Word
 - Status Register bits
- MEMORY BLOCKS
 - Boot Block (Bottom location)
 - Parameter and Main blocks
- BLOCK, MULTI-BLOCK and CHIP ERASE
- MULTI-BLOCK PROTECTION/TEMPORARY UNPROTECTION MODES
- ERASE SUSPEND and RESUME MODES
 - Read and Program another Block during Erase Suspend
- BYPASS MODE
 - Faster Programming Sequences
- LOW POWER CONSUMPTION
 - Stand-by and Automatic Stand-by
- 100,000 PROGRAM/ERASE CYCLES per BLOCK
- M28F102 COMPATIBLE
 - Pin-out and Read Mode
- 20 YEARS DATA RETENTION
 - Defectivity below 1ppm/year
- ELECTRONIC SIGNATURE
 - Manufacturer Code: 0020h
 - Device Code: 0097h

DESCRIPTION

The M29F102BB is a non-volatile memory that may be erased electrically at the block or chip level and programmed in-system on a Word-by-Word basis using only a single 5V V_{CC} supply. For Program and Erase operations the necessary high voltages are generated internally. The device can also be programmed in standard programmers.

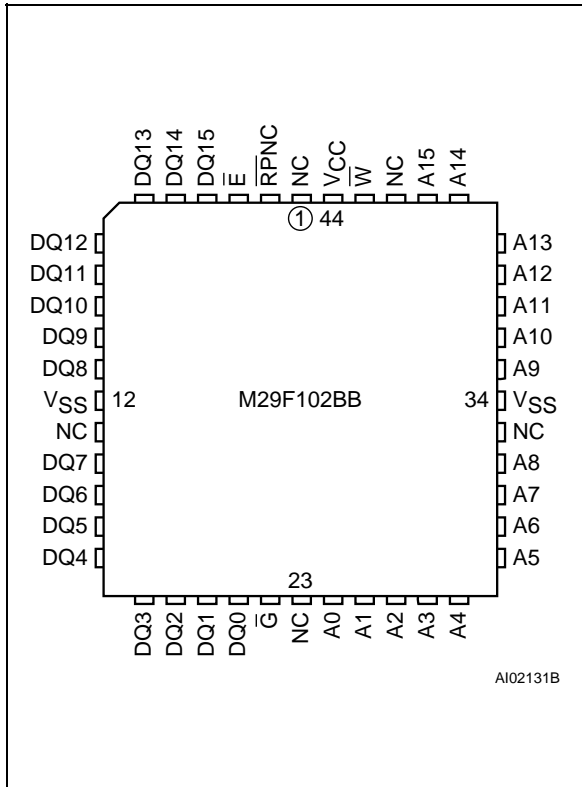


Logic Diagram



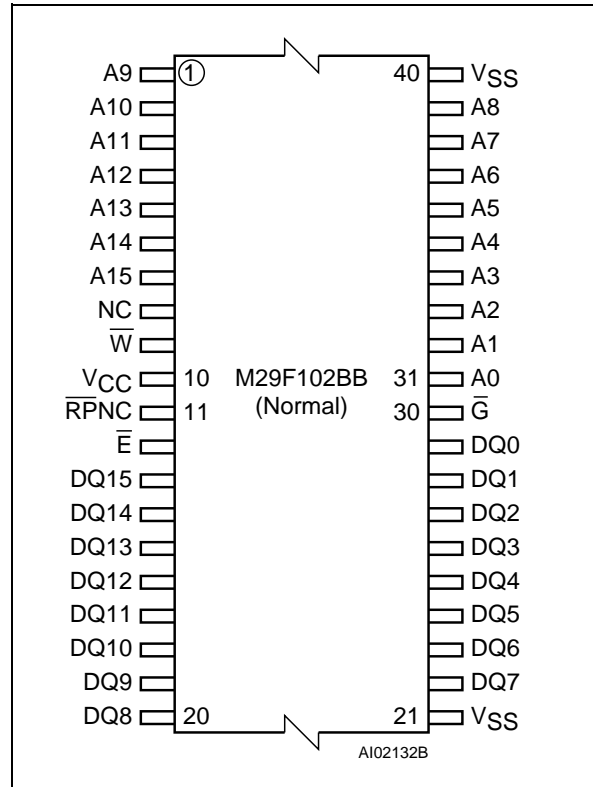
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LCC Pin Connections



Warning: NC = Not Connected.

TSOP Pin Connections

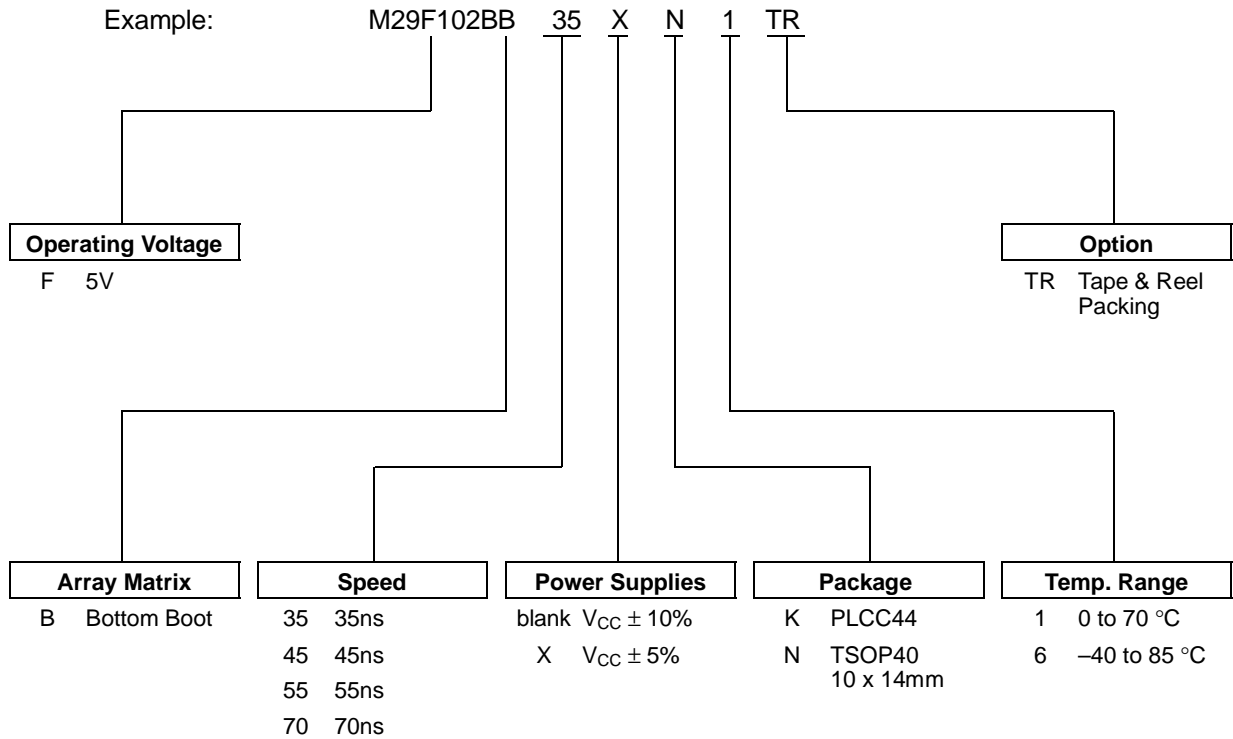


Warning: NC = Not Connected.

Signal Names

A0-A15	Address Inputs
DQ0-DQ7	Data Input/Outputs, Command Inputs
DQ8-DQ15	Data Input/Outputs
\bar{E}	Chip Enable
\bar{G}	Output Enable
\bar{W}	Write Enable
\bar{RPNC}	Reset / Block Temporary Unprotect
V _{CC}	Supply Voltage
V _{SS}	Ground

ORDERING INFORMATION SCHEME



Devices are shipped from the factory with the memory content erased (to FFFFh).

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.